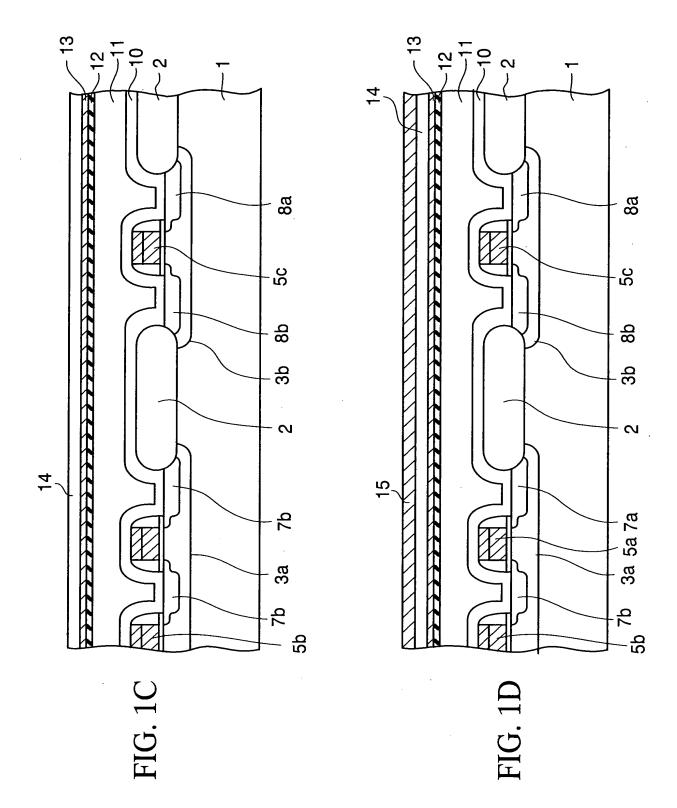
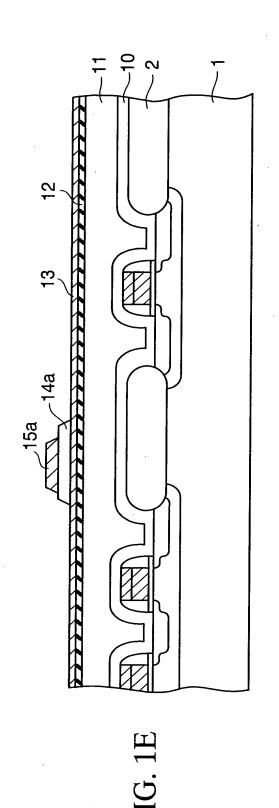
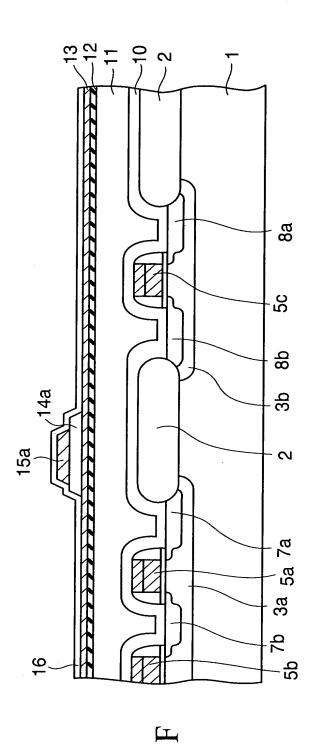


FIG. 1B







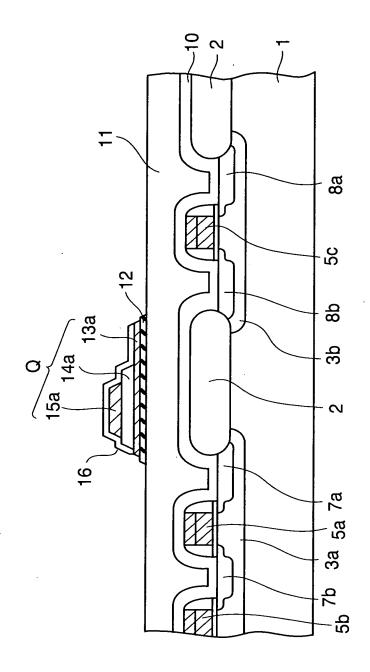
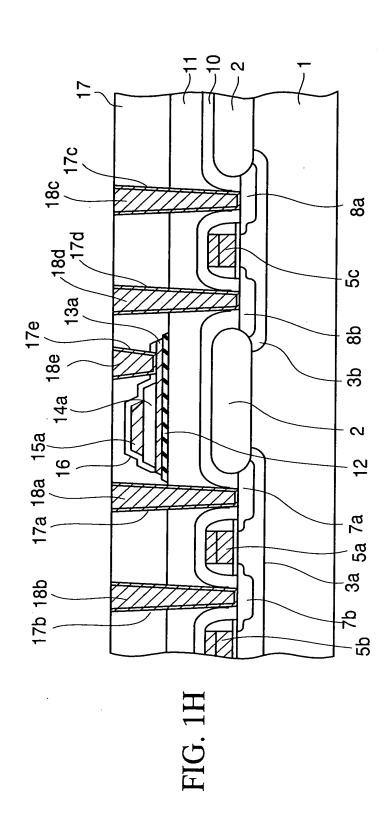
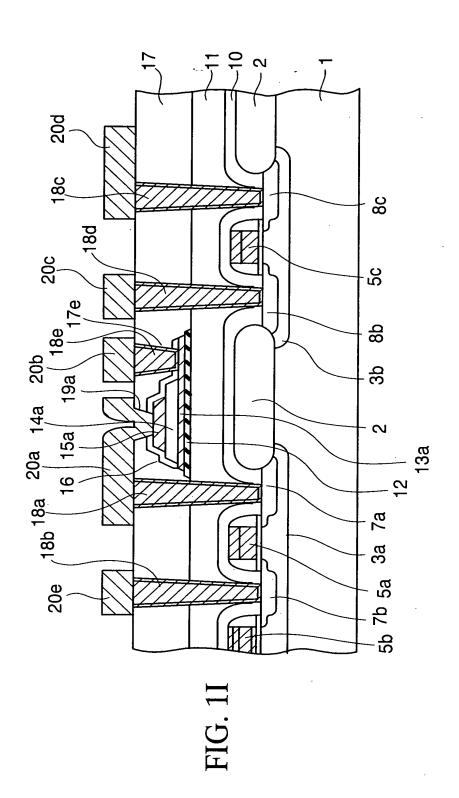
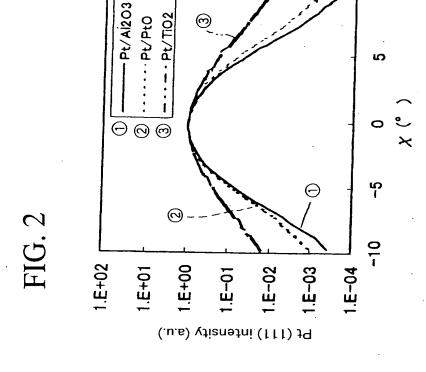
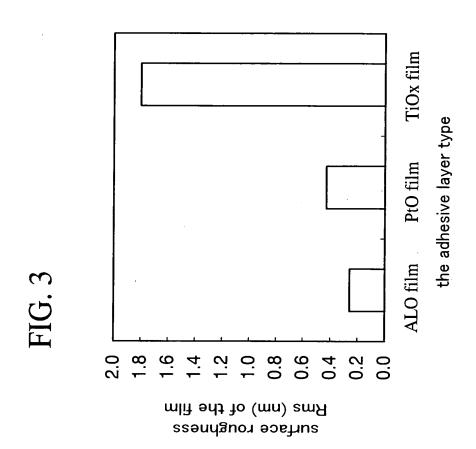


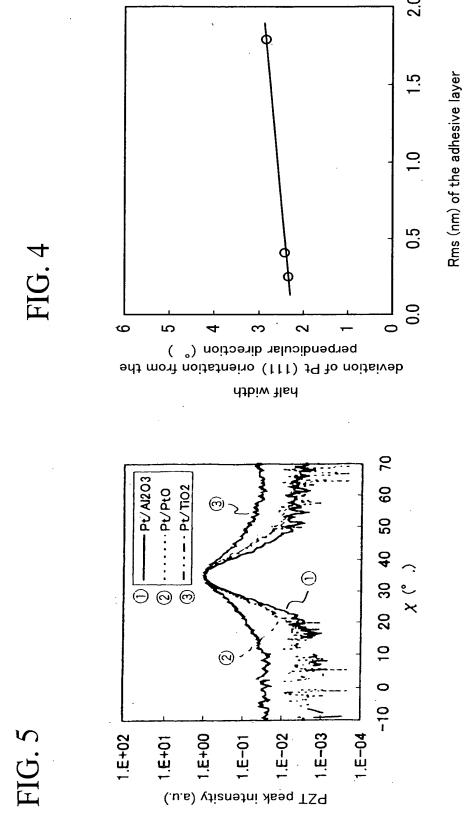
FIG. 1G











WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP Inventor: Tomohiro TAKAMATSU, et al. Attorney Docket: 032057

intensity ratio (Pt integrated intensity ratio of Ir doped PZT/Ir undoped PZT)

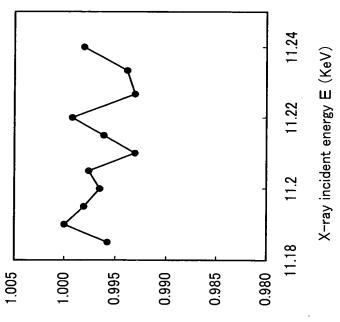
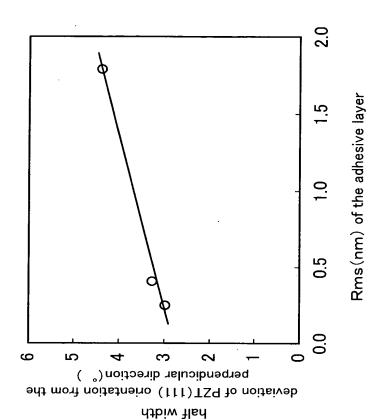
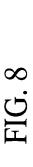
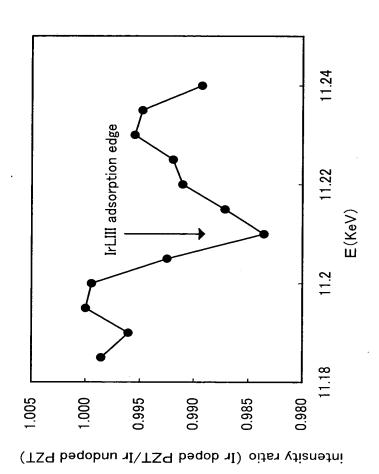


FIG. 6







crystal lattice of ABO_3 structure material according to the first embodiment of the present invention

A site atom •Bi, Pb, Ba, Sr, Ca, Na, K, Ir, rare earth element

B site atom
•Ti, Zr, Nb, Ta, W, Mn, Fe, Co, Cr, Ir

O atom

The Ir atom is contained in at least one of the A site atom and the B site atom.

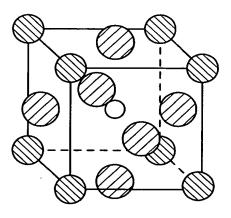
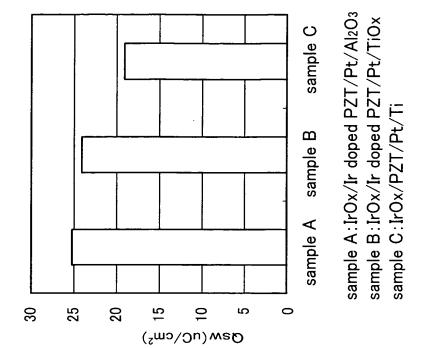
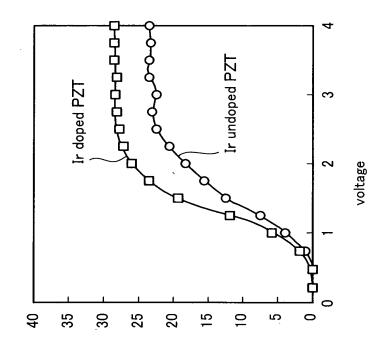


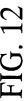
FIG. 11

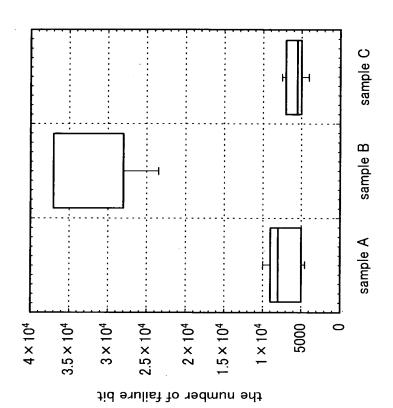


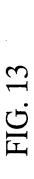
Rms of $Al_2O_3 = 0.23nm$ Rms of TiOx=1.8nm Rms of Ti=0.76nm



residual dielectric polarization charge (μ C/cm²)







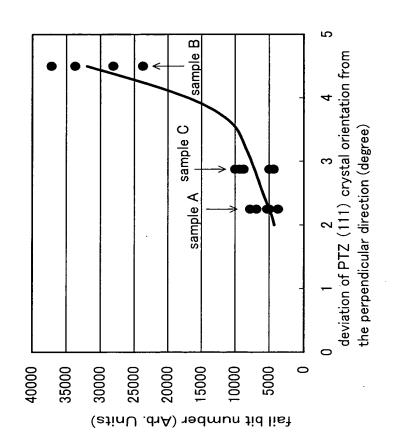
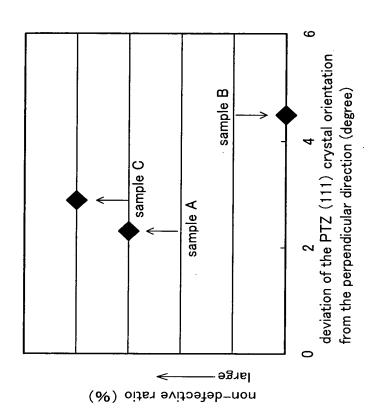


FIG. 15



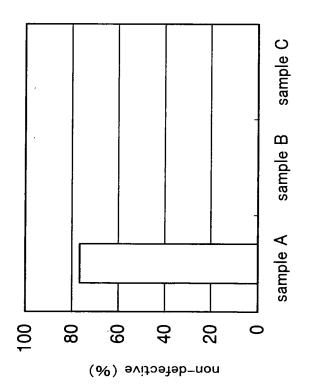


FIG. 16

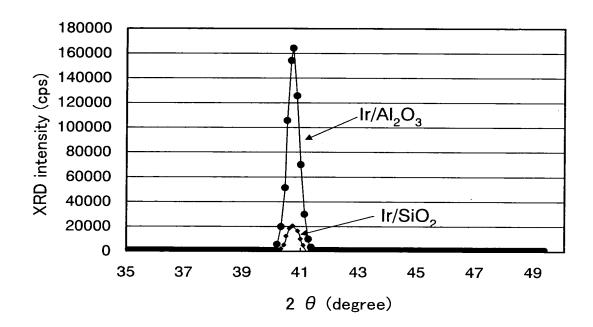


FIG. 17

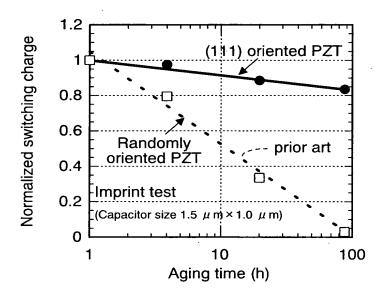


FIG. 18A

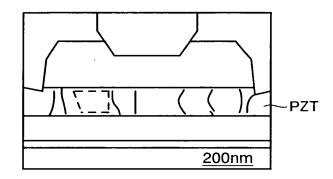


FIG. 18B

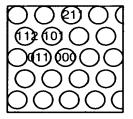


FIG. 19

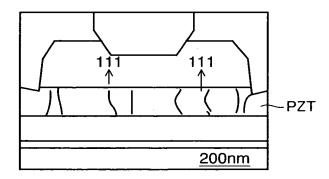


FIG. 20A

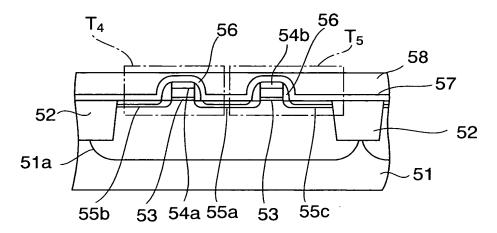


FIG. 20B

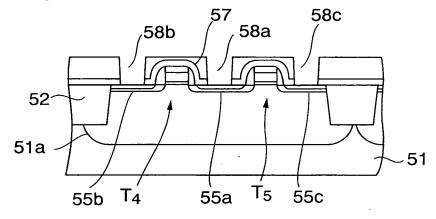
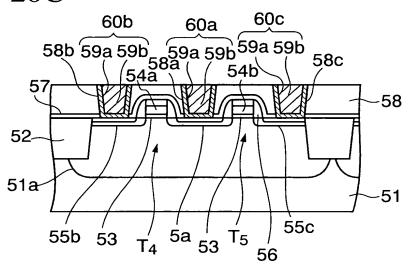


FIG. 20C



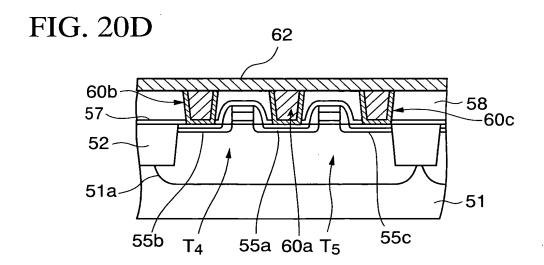


FIG. 20E

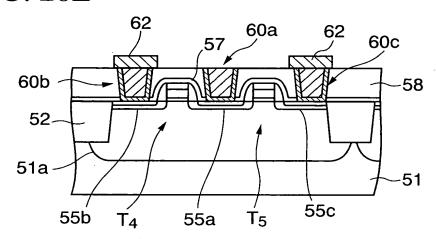


FIG. 20F

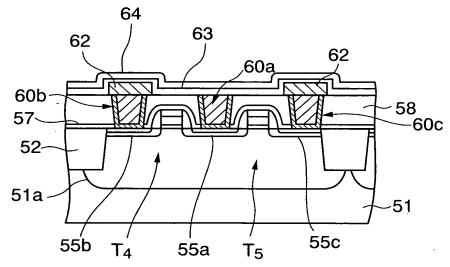


FIG. 20G

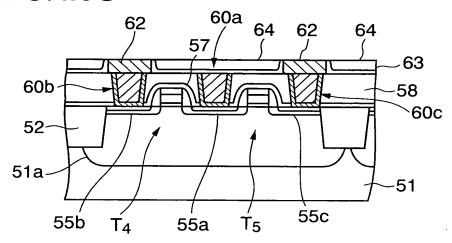


FIG. 20H

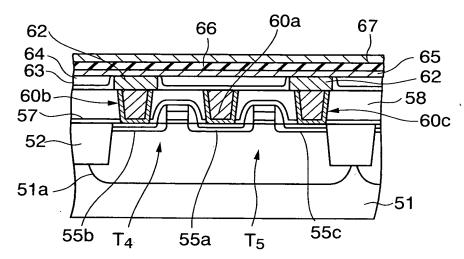
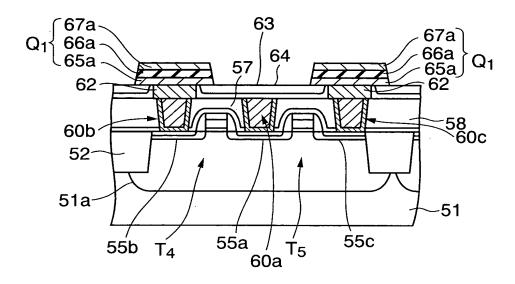


FIG. 20I



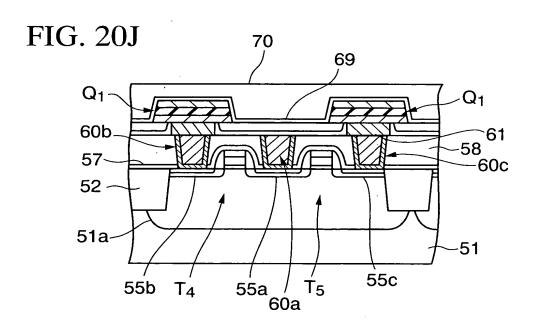


FIG. 20K

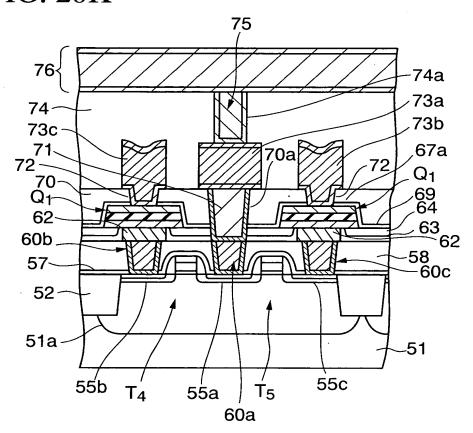


FIG. 21A

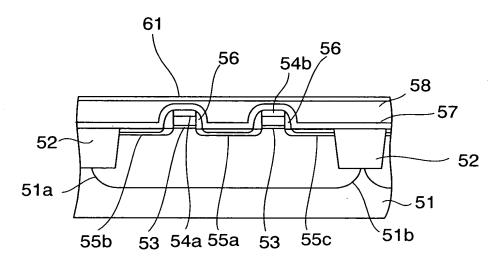
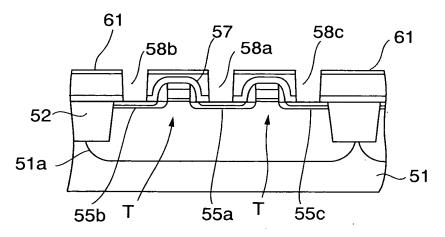


FIG. 21B



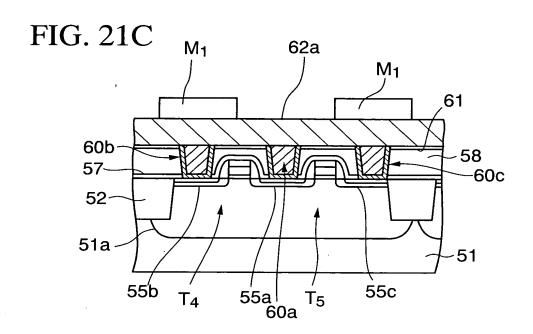


FIG. 21D

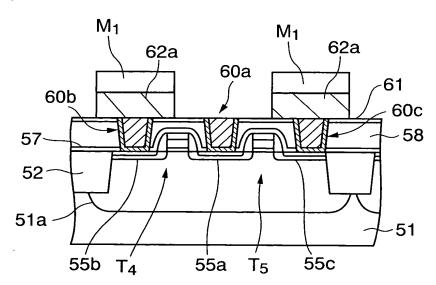


FIG. 21E

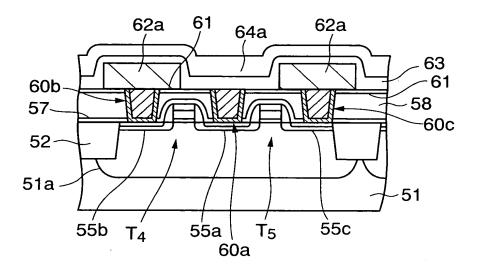
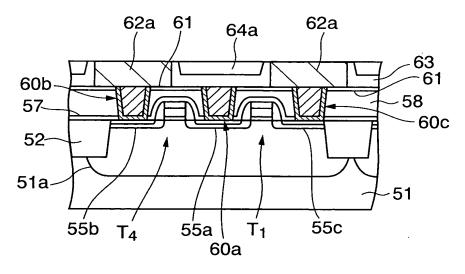
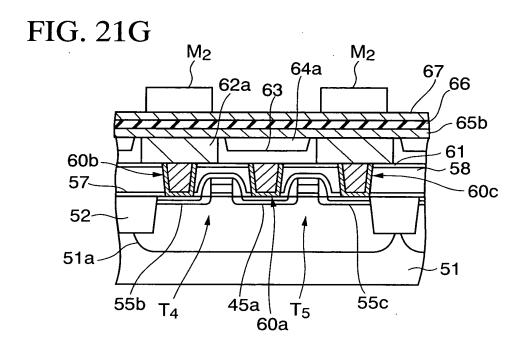


FIG. 21F





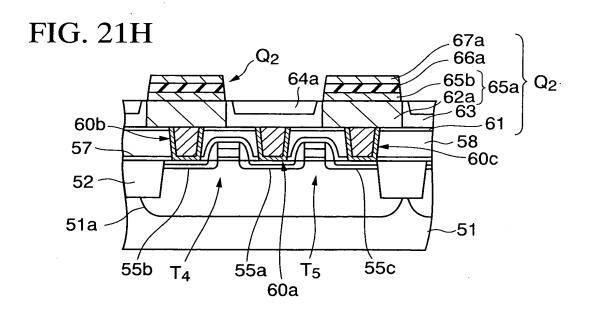


FIG. 21I

